

Silicon NPN Power Transistors

2SC1722

DESCRIPTION

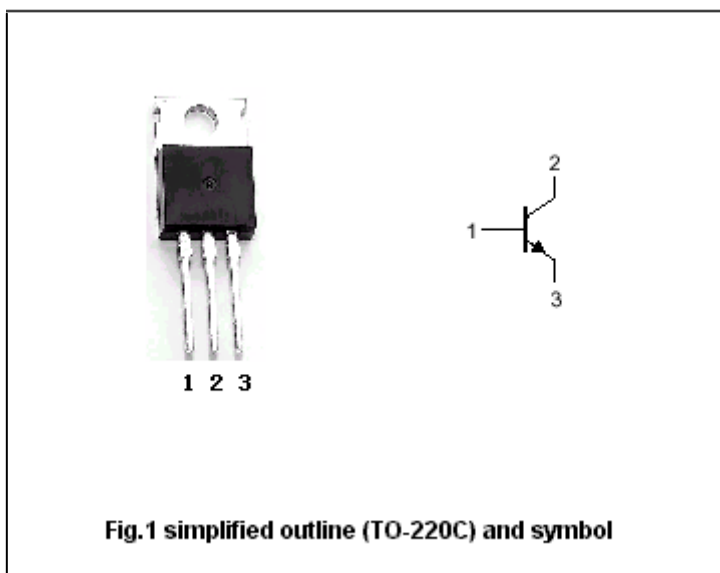
- With TO-220C package
- High breakdown voltage
- High transition frequency

APPLICATIONS

- Low frequency power amplifier
- TV horizontal/vertical driver

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.2	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	1.8	W
		$T_C=25^\circ\text{C}$	12.5	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-45~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA ; R _{BE} =∞	300			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =100 μ A ; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =100 μ A ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =50mA ; I _B =5mA		1.0	2.0	V
V _{BE}	Base-emitter on voltage	I _C =50m A ; V _{CE} =10V		0.68	0.9	V
I _{CBO}	Collector cut-off current	V _{CB} =250V ; I _E =0			0.1	μ A
I _{CEO}	Collector cut-off current	V _{CE} =250V ; R _{BE} =∞			2	μ A
h _{FE}	DC current gain	I _C =50m A ; V _{CE} =10V	50		300	
f _T	Transition frequency	I _C =30m A ; V _{CE} =20V		80		MHz
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =50V ; f=1MHz		4.3		pF

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PACKAGE OUTLINE

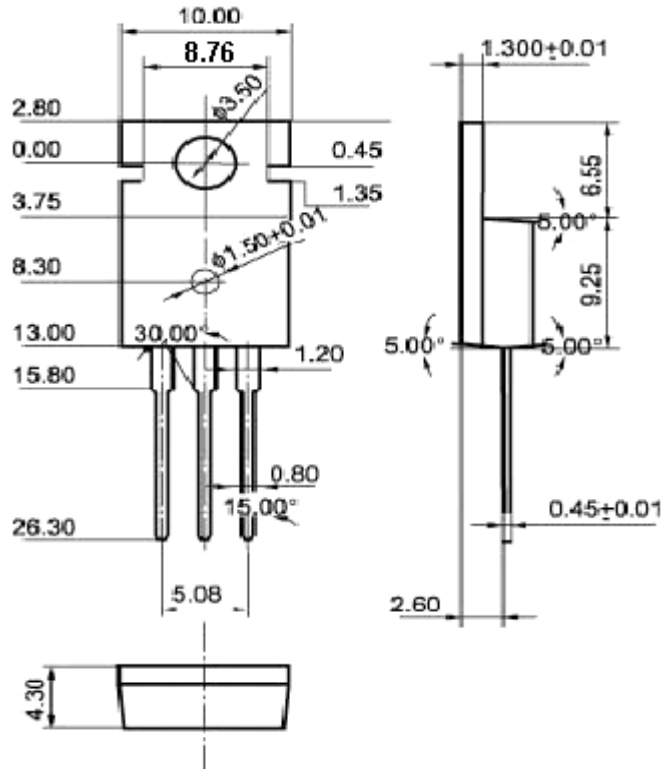


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)